

DESCRIPTION

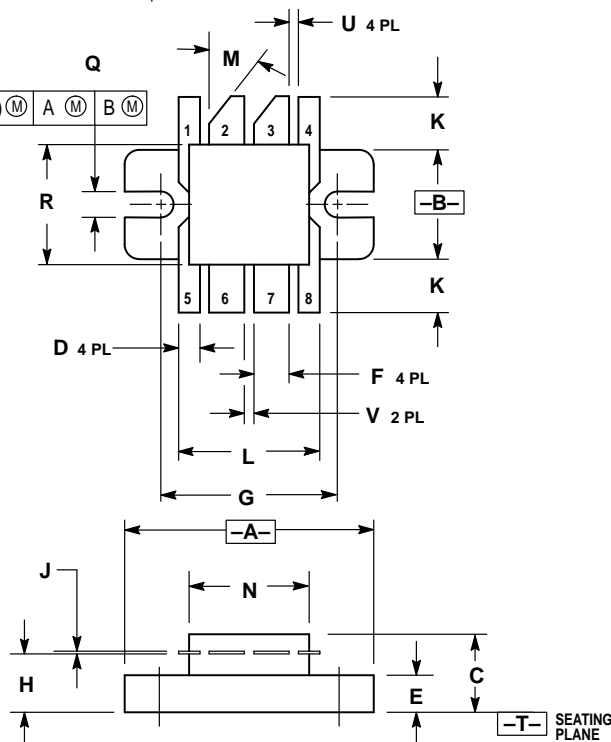
Designed for broadband applications up to 400 MHz frequency range. Primarily used as a driver or output amplifier in push-pul configurations.

FEATURES

- Output Power: 100 W
- Power Gain: 12 dB Typ@400M, 28V
- Efficiency: 60% Typ

DIMENSIONS

DIM	MILLIMETERS		INCHES		DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	22.60	23.11	0.890	0.910	K	4.34	4.90	0.171	0.193
B	9.52	10.03	0.375	0.395	L	12.45	12.95	0.490	0.510
C	6.65	7.16	0.262	0.282	M	45° NOM		45° NOM	
D	1.60	1.95	0.063	0.077	N	1.051	11.02	0.414	0.434
E	2.94	3.40	0.116	0.134	Q	3.04	3.35	0.120	0.132
F	2.87	3.22	0.113	0.127	R	9.90	10.41	0.390	0.410
G	16.51 BSC		0.650 BSC		U	1.02	1.27	0.040	0.050
H	4.01	4.36	0.158	0.172	V	0.64	0.89	0.025	0.035
J	0.07	0.15	0.003	0.006					



MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Drain-Gate Voltage	V_{DSS}	65	V
Drain-Gate Voltage(RGS=1.0M Ω)	V_{DGR}	65	V
Gate-Source Voltage	V_{GS}	± 40	V
Drain Current — Continuous	I_D	16	A
Total Device Dissipation	P_D	270	W
Junction Temperature	T_J	200	$^{\circ}C$
Storage Temperature Range	T_{STG}	-65 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=50mA, V_{GS}=0$	65	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=28V$	-	-	2	mAdc
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	1	uAdc
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=10V, I_D=50mA$	1.0	-	6.0	V
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_D=2A$	1.8	2.2	-	S
Input Capacitance	C_{iss}	$V_{DS}=28V, V_{GS}=0V, f=1.0MHz$	-	100	-	pF
Output Capacitance	C_{oss}		-	105	-	pF
Reverse Transfer Capacitance	C_{rss}		-	10	-	pF
Common Source Power Gain	G_p	$V_{DD}=28V, P_{OUT}=100W,$	10.0	12.0	-	dB
Drain Efficiency	η_D	$f=400MHz$	55.0	60.0	-	%

Note : Above parameters , ratings , limits and conditions are subject to change.